

# N-channel TrenchMOS standard level FET Rev. 2 — 2 February 2011

Product data sheet

#### **Product profile** 1.

# **1.1 General description**

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

# 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

### 1.4 Quick reference data

Table 1.	Quick reference	data				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	49	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	157	W
Static ch	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11;</u> see Figure 12	-	22	26	mΩ



### N-channel TrenchMOS standard level FET

Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 49 \text{ A};  V_{sup} \leq 100  \text{V}; \\ R_{GS} &= 50  \Omega;   V_{GS} = 10  \text{V}; \\ T_{j(init)} &= 25 ^\circ\text{C};  \text{unclamped} \end{split} $	-	-	144	mJ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 80 V; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	13	-	nC

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

# 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK7626-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

N-channel TrenchMOS standard level FET

# 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		<b>3,</b> (			
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	49	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	34	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <u>Figure 3</u>	-	197	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	157	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	49	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$	-	197	А
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 49 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped	-	144	mJ

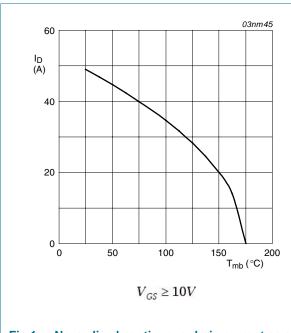
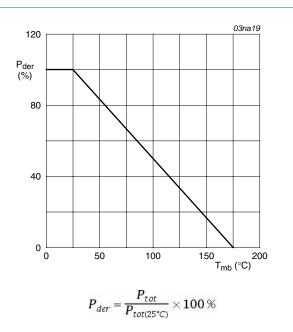


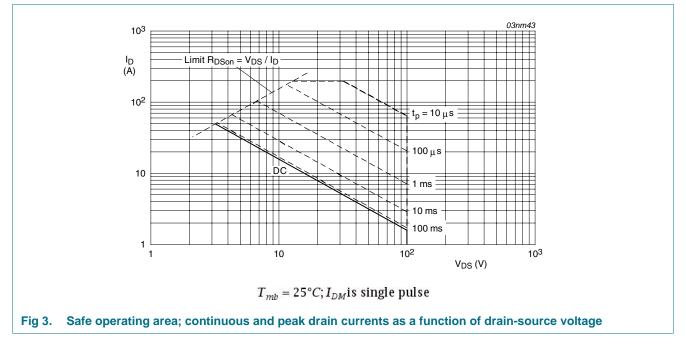
Fig 1. Normalized continuous drain current as a function of mounting base temperature





# BUK7626-100B

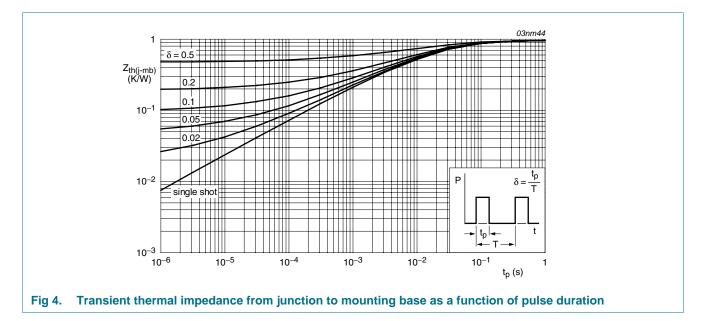
### N-channel TrenchMOS standard level FET



# 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	-	50	K/W



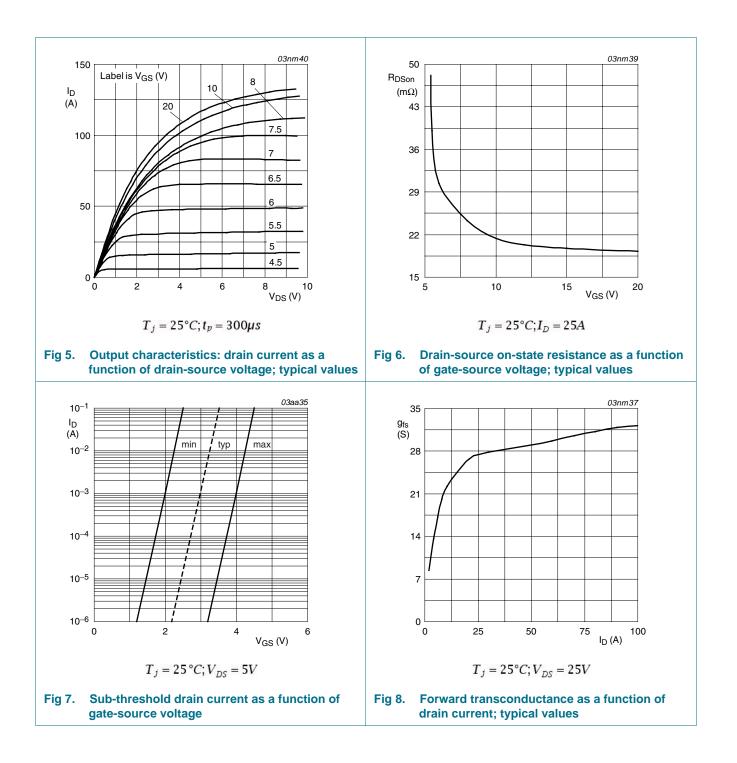
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# 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
•		Conditions	IVIIII	тур	WIAX	Unit
Static chara		1 = 0.25 = 0.11 = 0.14 = -25 °C	100			V
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = -55 ^{\circ}\text{C}$		-	-	V
N/			89	-	-	V
	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 10</u>	1	-	-	-
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u>	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
Doon	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see Figure 11; see Figure 12	-	-	65	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see Figure 11; see Figure 12	-	22	26	mΩ
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 10 V;	-	38	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	9	-	nC
Q <sub>GD</sub>	gate-drain charge		-	13	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	2168	2891	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	238	286	pF
C <sub>rss</sub>	reverse transfer capacitance		-	102	140	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_{L}$ = 1.2 $\Omega$ ; $V_{GS}$ = 10 V;	-	21	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C	-	40	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	47	-	ns
t <sub>f</sub>	fall time		-	19	-	ns
L <sub>D</sub>	internal drain inductance	from drain lead 6 mm from package to centre of die; T <sub>i</sub> = 25 °C	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die; T <sub>i</sub> = 25 °C	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead 6 mm from package to source bond pad; $T_i = 25 ^{\circ}\text{C}$	-	7.5	-	nH
Source-drai	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see Figure 15	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs;	-	94	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	_	115	-	nC

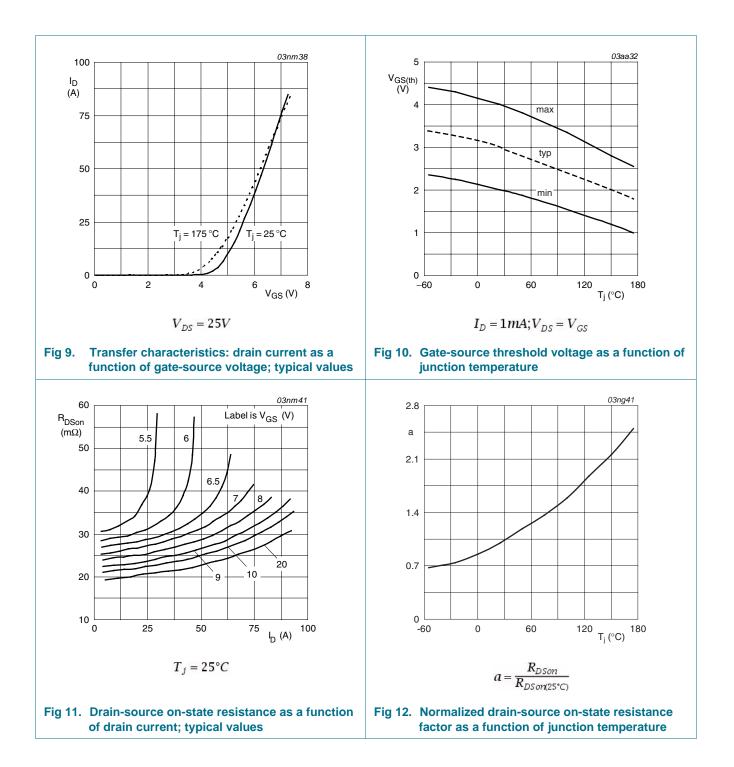
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### N-channel TrenchMOS standard level FET



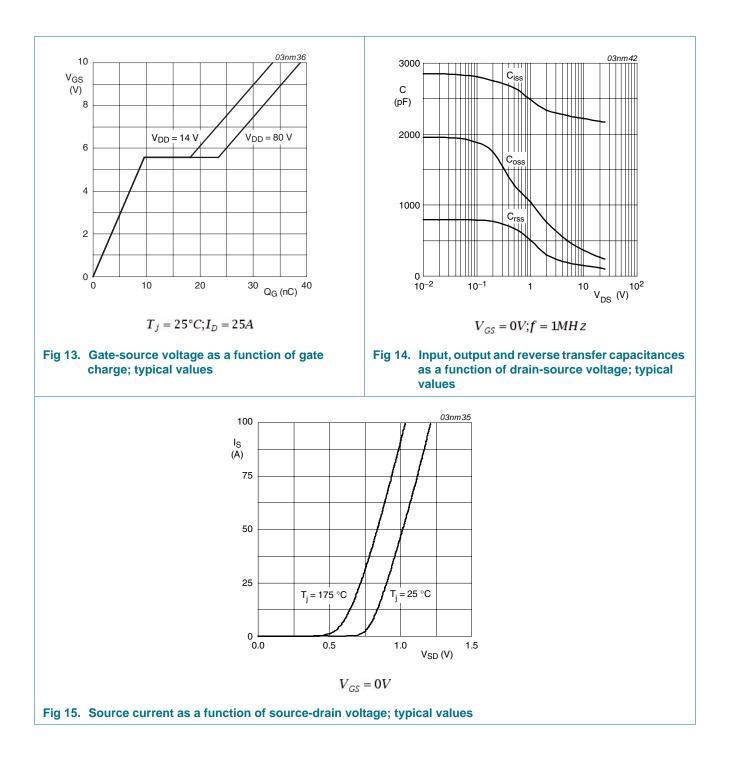
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# BUK7626-100B

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BUK7626-100B

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# 7. Package outline

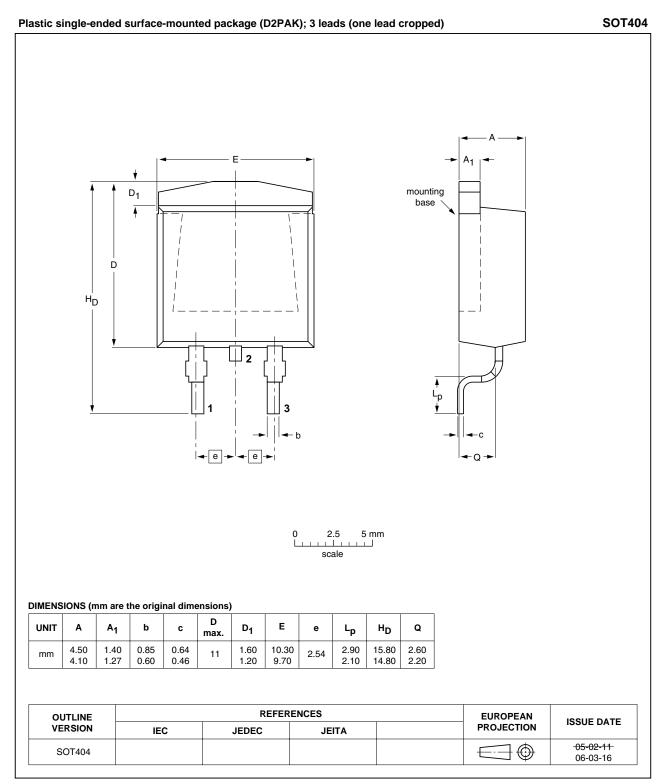


Fig 16. Package outline SOT404 (D2PAK)

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BUK7626-100B

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# 8. Revision history

Table 7. Revision hi	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7626-100B v.2	20110202	Product data sheet	-	BUK75_7626_100B-01
Modifications:	<ul> <li>The format of this of NXP Semiconduction</li> </ul>	lata sheet has been rede ctors.	signed to comply with the	e new identity guidelines
	<ul> <li>Legal texts have be</li> </ul>	een adapted to the new co	ompany name where app	propriate.
	<ul> <li>Type number BUK</li> </ul>	7626-100B separated fror	n data sheet BUK75_762	26_100B-01.
BUK75_7626_100B-01 (9397 750 11238)	20030411	Product data	-	-

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### N-channel TrenchMOS standard level FET

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### N-channel TrenchMOS standard level FET

# 11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status11
9.2	Definitions
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12



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